L Number	Hits	Search Text	DB	Time stamp
15	1148199	(((((soi or (silicon adj on adj	USPAT;	2002/06/11 15:42
13	12.02.0	insulator)) and (single-crystal adj	US-PGPUB;	
		silicon)) and anneal\$3) and substrate) and	EPO; JPO;	Į
		reduc\$3 adj atmosphere) and nonporous and	DERWENT;	į
		active region	IBM TDB	
16	l ol	(((((soi or (silicon adj on adj	USPAT;	2002/06/11 15:38
100	_	insulator)) and (single-crystal adj	US-PGPUB;	
	1	silicon)) and anneal\$3) and substrate) and	EPO; JPO;	Į.
		reduc\$3 adj atmosphere) and nonporous and	DERWENT;	
		active adj region	IBM TDB	
17	0	(((((soi or (silicon adj on adj	USPĀT;	2002/06/11 15:39
1 - '	_	insulator)) and (single-crystal adj	US-PGPUB;	
		silicon)) and anneal\$3) and substrate) and	EPO; JPO;	
		reduc\$3 adj atmosphere) and nonporous and	DERWENT;	
		transistor with active adj region	IBM TDB	
18	0	(((((soi or (silicon adj on adj	USPAT;	2002/06/11 15:40
		insulator)) and (single-crystal adj	US-PGPUB;	
		silicon)) and anneal\$3) and substrate) and	EPO; JPO;	
		reduc\$3 adj atmosphere) and nonporous and	DERWENT;	İ
		tft	IBM TDB	
19	20	nonporous and tft	USPĀT;	2002/06/11 15:40
1		•	US-PGPUB;	
			EPO; JPO;	1
			DERWENT;	
			IBM TDB	
20	9	(((((soi or (silicon adj on adj	USPAT;	2002/06/11 15:43
20		insulator)) and (single-crystal adj	US-PGPUB;	
		silicon)) and anneal\$3) and substrate) and	EPO; JPO;	l i
		reduc\$3 adj atmosphere) and nonporous	DERWENT;	
		2000040 and memorphisms, seems 1	IBM TDB	
21	1	(((((soi or (silicon adj on adj	USPAT;	2002/06/11 15:44
21	_	insulator)) and (single-crystal adj	US-PGPUB;	
		silicon)) and anneal\$3) and substrate) and	EPO; JPO;	
		reduc\$3 adj atmosphere) and nonporous) and	DERWENT;	
		(tft or (thin adj film adj transistor))	IBM TDB	
22	1	(010 01 (01111 111)	USPAT;	2002/06/11 15:48
22	_		US-PGPUB	
23	1		USPAT;	2002/06/11 16:01
			US-PGPUB	
_	673	((438/311) or (438/149) or (438/150) or	USPAT;	2002/06/10 17:05
		(438/378)).CCLS.	US-PGPUB	
_	339	(((438/311) or (438/149) or (438/150) or	USPAT;	2002/06/10 17:05
		(438/378)).CCLS.) and anneal\$3	US-PGPUB	
_	106	((((438/311) or (438/149) or (438/150) or	USPAT;	2002/06/10 17:06
		(438/378)).CCLS.) and anneal\$3) and (soi	US-PGPUB	
		or (silicon adj on adj insulator))		0000/06/10 00 10
-	12		USPAT;	2002/06/10 20:12
		(438/378)).CCLS.) and anneal\$3) and (soi	US-PGPUB	
		or (silicon adj on adj insulator))) and		
		(single-crystal adj silicon)		0000/06/10 55 15
-	469		USPAT;	2002/06/10 20:13
	1	and (single-crystal adj silicon)	US-PGPUB	0000/06/10 00 10
-	595	(soi or (silicon adj on adj insulator))	USPAT;	2002/06/10 20:13
1		and (single-crystal adj silicon)	US-PGPUB;	
			EPO; JPO;	
	1		DERWENT;	
			IBM_TDB	0000 406 410 00 10
-	289		USPAT;	2002/06/10 20:13
		and (single-crystal adj silicon)) and	US-PGPUB;	
		anneal\$3	EPO; JPO;	
			DERWENT;	
			IBM_TDB	0000/06/10 00 11
-	285	(((soi or (silicon adj on adj insulator))	USPAT;	2002/06/10 20:14
		and (single-crystal adj silicon)) and	US-PGPUB;	
		anneal\$3) and substrate	EPO; JPO;	
			DERWENT;	
1			IBM_TDB	

-	28	, , , , ,	USPAT;	2002/06/10 20:15
		and (single-crystal adj silicon)) and	US-PGPUB;	
		anneal\$3) and substrate) and reduc\$3 adj	EPO; JPO;	
		atmosphere	DERWENT;	
		•	IBM TDB	
l _	9	(((((soi or (silicon adj on adj	USPAT;	2002/06/11 15:36
	-	insulator)) and (single-crystal adj	US-PGPUB;	
		silicon)) and anneal\$3) and substrate) and	EPO; JPO;	
		reduc\$3 adj atmosphere) and nonporous	DERWENT;	
		and the same of th	IBM TDB	

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